

MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK7P60W

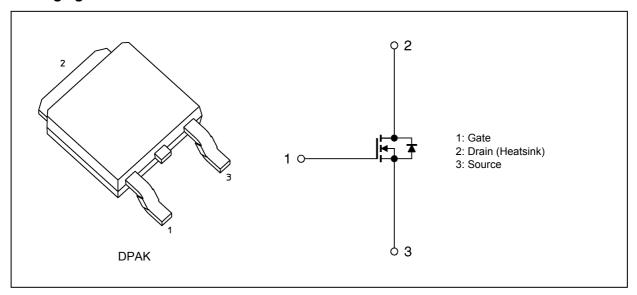
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)}$ = 0.5 Ω (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 2.7 to 3.7 V (V_{DS} = 10 V, I_D = 0.35 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	600	V
Gate-source voltage		V_{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	7.0	Α
Drain current (pulsed)	(Note 1)	I _{DP}	28	
Power dissipation (T _c = 25	°C)	P_{D}	60	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	92	mJ
Avalanche current		I _{AR}	1.8	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	7.0	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	28	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	2.09	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 49.9 mH, R_G = 25 Ω , I_{AR} = 1.8 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

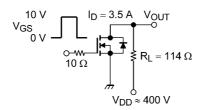
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 0.35 mA	2.7	_	3.7	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 3.5 A	_	0.5	0.6	Ω

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz	_	490	_	pF
Reverse transfer capacitance	C _{rss}		_	1.7	_	
Output capacitance	C _{oss}		_	13	_	
Effective output capacitance	C _{o(er)}	V _{DS} = 0 to 400 V, V _{GS} = 0 V	_	21	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	7.0	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	18	_	ns
Switching time (turn-on time)	t _{on}		_	40	_	
Switching time (fall time)	t _f		_	7.0	_	
Switching time (turn-off time)	t _{off}		_	55		
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 3.5 A	25	_		V/ns



Duty \leq 1%, $t_W=10~\mu s$

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 7.0 \text{ A}$	_	15		nC
Gate-source charge 1	Q _{gs1}			3.2		
Gate-drain charge	Q_{gd}		_	8.0	_	

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 7.0 A, V _{GS} = 0 V		_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 3.5 A, V _{GS} = 0 V	_	230	_	ns
Reverse recovery charge	Q_{rr}	-dI _{DR} /dt = 100 A/μs		1.7	_	μС
Peak reverse recovery current	I _{rr}		_	16		Α
Diode dv/dt ruggedness	dv/dt	I _{DR} = 3.5 A, V _{GS} = 0 V, V _{DD} = 400 V	15	_		V/ns



7. Marking

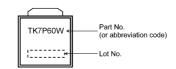
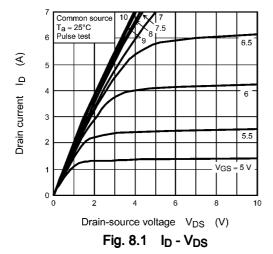
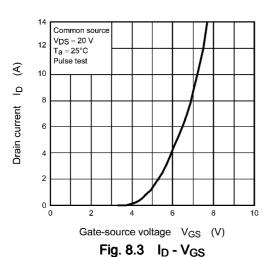


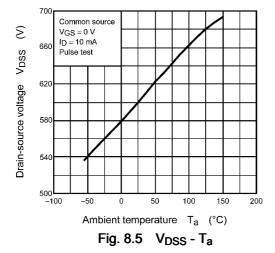
Fig. 7.1 Marking

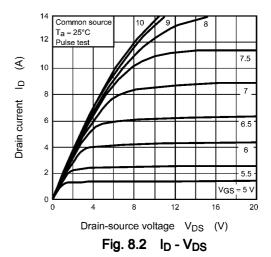
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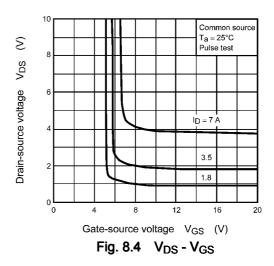
8. Characteristics Curves (Note)











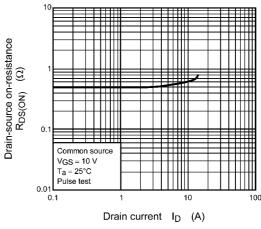


Fig. 8.6 $R_{DS(ON)}$ - I_D

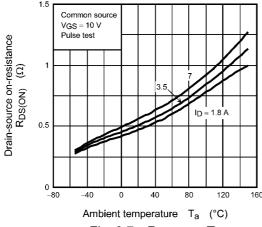


Fig. 8.7 R_{DS(ON)} - T_a

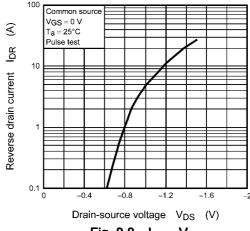


Fig. 8.8 I_{DR} - V_{DS}

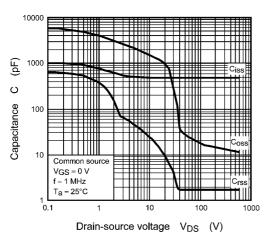


Fig. 8.9 C - V_{DS}

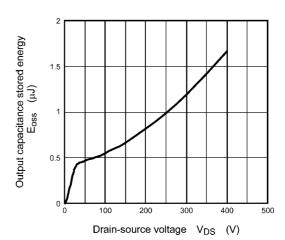


Fig. 8.10 E_{OSS} - V_{DS}

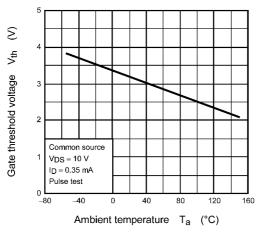


Fig. 8.11 V_{th} - T_a

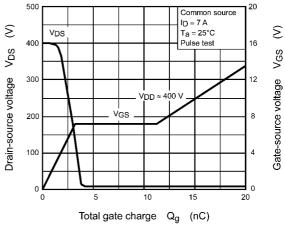


Fig. 8.12 Dynamic Input/Output Characteristics

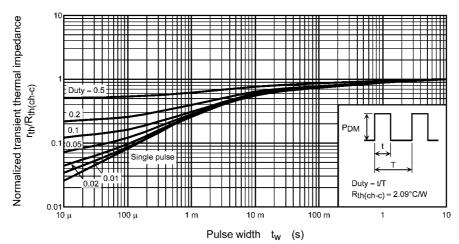


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

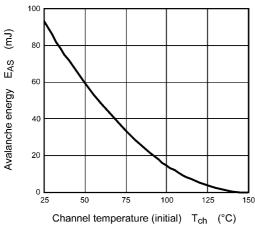


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

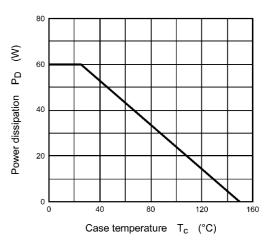
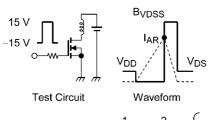


Fig. 8.15 P_D - T_c (Guaranteed Maximum)



 $R_G = 25 \Omega$, $V_{DD} = 90 V$ $E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$

Fig. 8.16 Test Circuit/Waveform

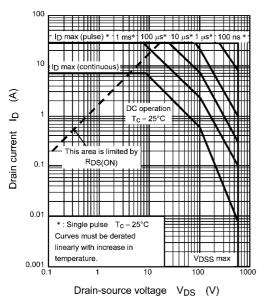


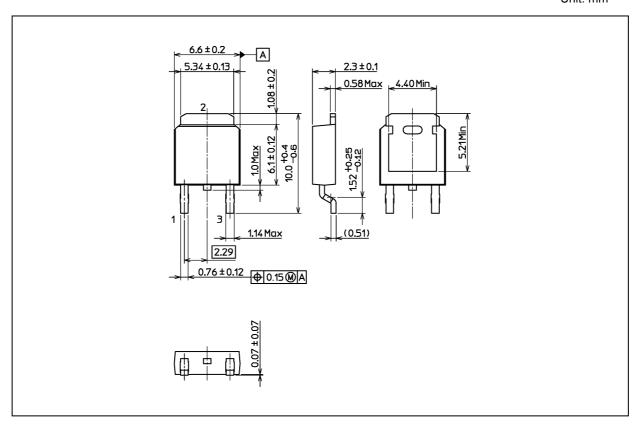
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

Package Name(s)
TOSHIBA: 2-7K1S
Nickname: DPAK



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